

Silicon PNP Power Transistors

2SA1095

DESCRIPTION

- With MT-200 package
- Complement to type 2SC2565
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Power amplifier applications
- Recommended for 100W high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

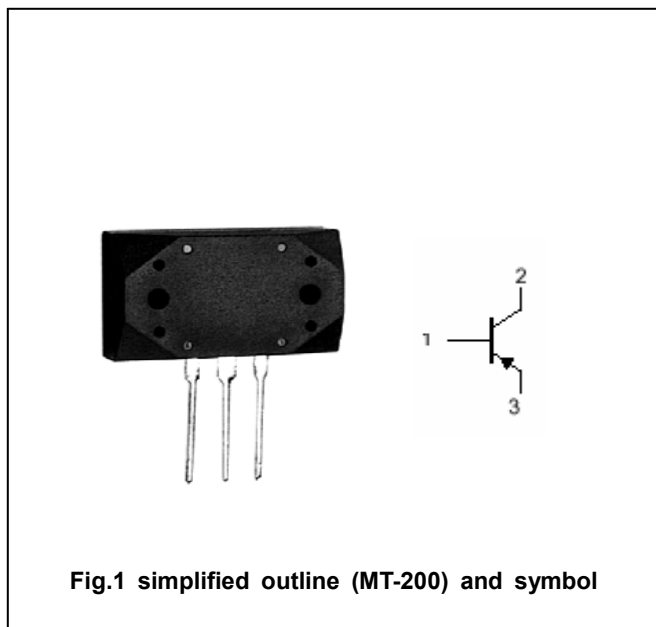


Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-160	V
V _{CEO}	Collector-emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-15	A
I _E	Emitter current		15	A
P _C	Collector power dissipation	T _C =25°C	150	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-100mA; I _B =0	-160			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5 A; I _B =-0.5 A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-5A; V _{CE} =-5V			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-160V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-50	μA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-5V	55		240	
h _{FE-2}	DC current gain	I _C =-5A; V _{CE} =-5V	40			
f _T	Transition frequency	I _C =-1A; V _{CE} =-10V		60		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		350		pF

◆ h_{FE} classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

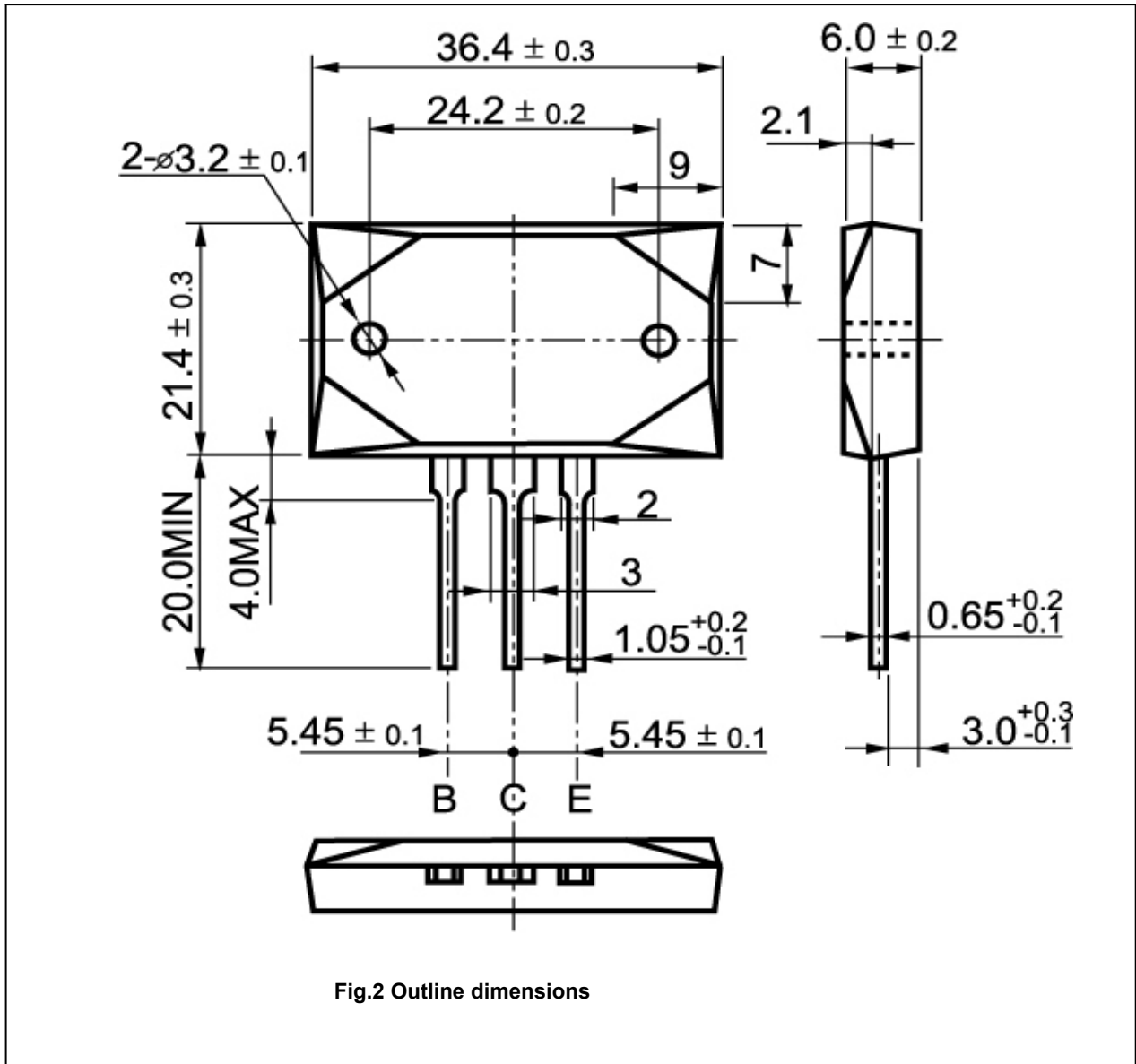


Fig.2 Outline dimensions